Switching Diode, Dual, High Voltage, Common Cathode

BAV23CL, NSVBAV23CL

Features

- Moisture Sensitivity Level: 1
- ESD Rating Human Body Model: Class 2
 - Machine Model: Class C
- Fast Switching Speed
- Switching Application
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- LCD TV
- Power Supply
- Industrial

MAXIMUM RATINGS

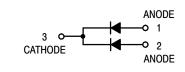
Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V _R	250	V
Repetitive Peak Reverse Voltage	V_{RRM}	250	V
Peak Forward Current	IF	400	mA
	I _{FSM}	9.0 3.0 1.7	Α
Peak Forward Surge Current	I _{FM(surge)}	625	mAdc
Non-Repetitive Peak Per Human Body Model Per Machine Model	HBM MM	4.0 400	kV V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



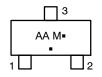
ON Semiconductor®

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MARKING DIAGRAM



AA = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BAV23CLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAV23CLT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
NSVBAV23CLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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BAV23CL, NSVBAV23CL

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
SINGLE HEATED			•
Total Device Dissipation (Note 1) T _A = 25°C Derate above 25°C	P _D	265 2.1	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	472	°C/W
Thermal Reference, Junction-to-Anode Lead (Note 1)	R_ψ _{JL}	263	°C/W
Thermal Reference, Junction-to-Case (Note 1)	R_ψ _{JC}	289	°C/W
Total Device Dissipation (Note 2) T _A = 25°C Derate above 25°C	P _D	345 2.7	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	362	°C/W
Thermal Reference, Junction-to-Anode Lead (Note 2)	R_ψ _{JL}	251	°C/W
Thermal Reference, Junction-to-Case (Note 2)	R_ψ _{JC}	250	°C/W
DUAL HEATED (Note 3)		•	
Total Device Dissipation (Note 1) T _A = 25°C Derate above 25°C	P _D	390 3.1	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ hetaJA}$	321	°C/W
Thermal Reference, Junction-to-Anode Lead (Note 1)	R_ψ _{JL}	159	°C/W
Thermal Reference, Junction-to-Case (Note 1)	R_ψ _{JC}	138	°C/W
Total Device Dissipation (Note 2) T _A = 25°C Derate above 25°C	P _D	540 4.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	231	°C/W
Thermal Reference, Junction-to-Anode Lead (Note 2)	R_ψ _{JL}	148	°C/W
Thermal Reference, Junction-to-Case (Note 2)	R_ψ _{JC}	119	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

- FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 2 oz. copper traces, still air.
- 3. Dual heated values assume total power is sum of two equally powered channels

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

(A	,			
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u>, </u>	•	•	
Reverse Voltage Leakage Current (V _R = 200 Vdc) (V _R = 200 Vdc, T _J = 150°C)	I _R	_ _	0.1 100	μAdc
Reverse Breakdown Voltage (I _{BR} = 100 μAdc)	V _(BR)	250	_	Vdc
Forward Voltage (I _F = 100 mAdc) (I _F = 200 mAdc)	V _F	- -	1000 1250	mV
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _T	-	5.0	pF
Reverse Recovery Time (I _F = I _R = 30 mAdc, R _L = 100 Ω)	t _{rr}	-	150	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BAV23CL, NSVBAV23CL

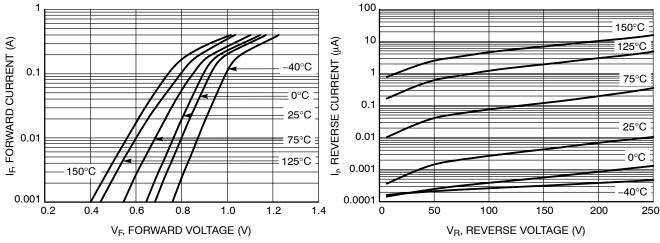


Figure 1. Forward Voltage

Figure 2. Reverse Current

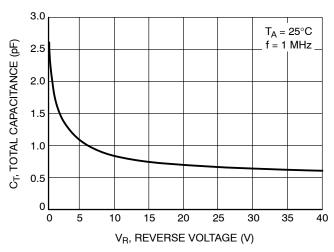
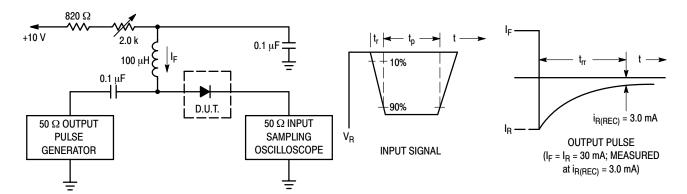


Figure 3. Total Capacitance



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 30 mA.

2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.

3. $t_p \gg t_{rr}$

Figure 4. Recovery Time Equivalent Test Circuit



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	ANODE	3. GATE	ANODE

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
CATHODE	CATHODE	2. ANODE	CATHODE	2. ANODE	ANODE
ANODE	CATHODE	CATHODE	ANODE	CATHODE-ANOD	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	NO CONNECTION

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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